

SILICON DETECTOR & MIXER DIODE

1SS99

DESCRIPTION The 1SS99 is silicon epitaxial schottky barrier diode, especially designed for mixing, log or A-D converting, video detecting, frequency discriminating, sampling and wave shaping.

FEATURES

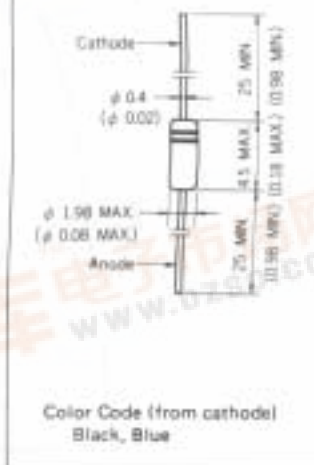
- Small size glass package. (DO-35 TYPE)
- Low noise figure.
- Low turn-on voltage.
 $V_F=0.23\text{ V MAX. at } I_F=1\text{ mA}$
- Low capacitance.
 $C_1=0.9\text{ pF MAX. at } 1\text{ MHz, } V_R=0.2\text{ V}$
- Low cost.

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures		
Junction Temperature	T_j	175 °C
Storage Temperature	T_{stg}	-65 to +175 °C
Maximum Power Dissipation ($T_a=25\text{ °C}$)		
Power Dissipation	P_T	150 mW
Maximum Voltage and Current ($T_a=25\text{ °C}$)		
Peak Reverse Voltage	V_{RM}	5.0 V
Forward Current	I_F	30 mA
Reverse Burnout*	B_D	2.0 erg

Note* : Capacitor charge method C(charge)=25 pF

PACKAGE DIMENSIONS
in millimeters (inches)



ELECTRICAL CHARACTERISTICS ($T_a=25\text{ °C}$)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
I_R	Reverse Current			25	μA	$V_R=0.5\text{ V}$
V_F	Forward Voltage			0.23	V	$I_F=1.0\text{ mA}$
I_F	Forward Current	30			mA	$V_F=0.5\text{ V}$
C_1	Capacitance			0.9	pF	$V_R=0.2\text{ V, } f=1\text{ MHz}$

[查询"1SS99"供应商](#)

TYPICAL CHARACTERISTICS (Ta=25 °C)

